

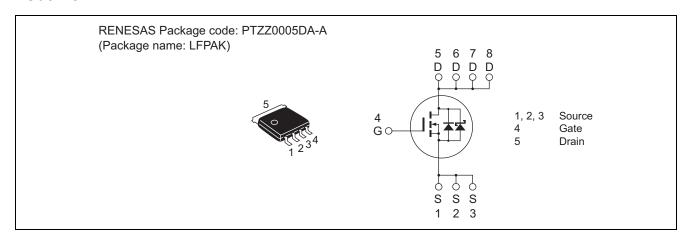
RJK03C1DPB

Silicon N Channel Power MOS FET with Schottky Barrier Diode Power Switching REJ03G1830-0310 Rev.3.10 Sep 29, 2009

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 1.7 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V)}$
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	60	Α
Drain peak current	I _{D(pulse)} Note1	240	Α
Body-drain diode reverse drain current	I_{DR}	60	Α
Avalanche current	I _{AP} Note 2	28	Α
Avalanche energy	E _{AR} Note 2	78.4	mJ
Channel dissipation	Pch Note3	65	W
Channel to Case Thermal Resistance	θch-C	1.92	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. Tc = 25°C

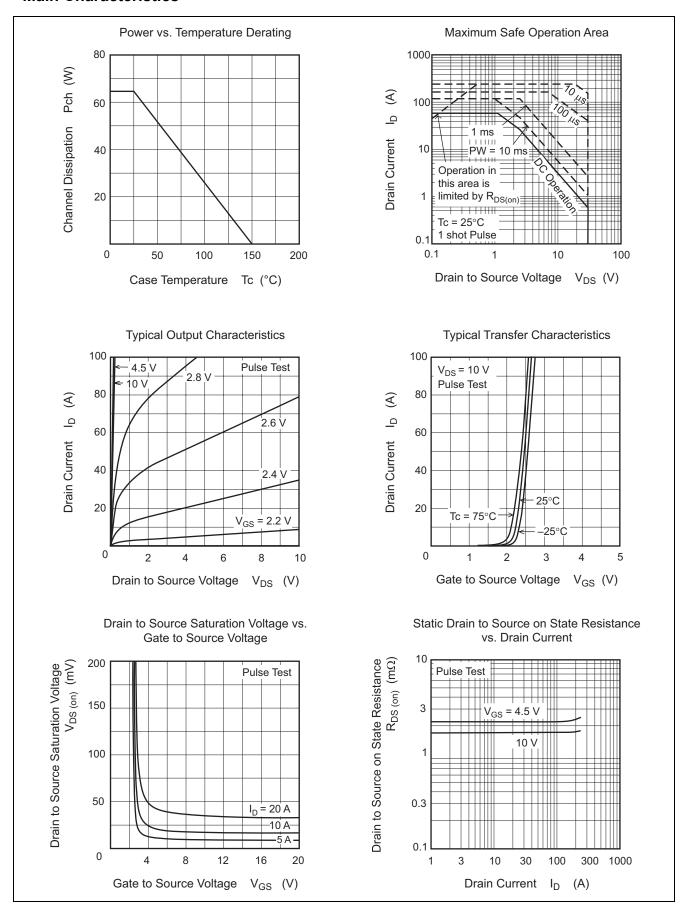
Electrical Characteristics

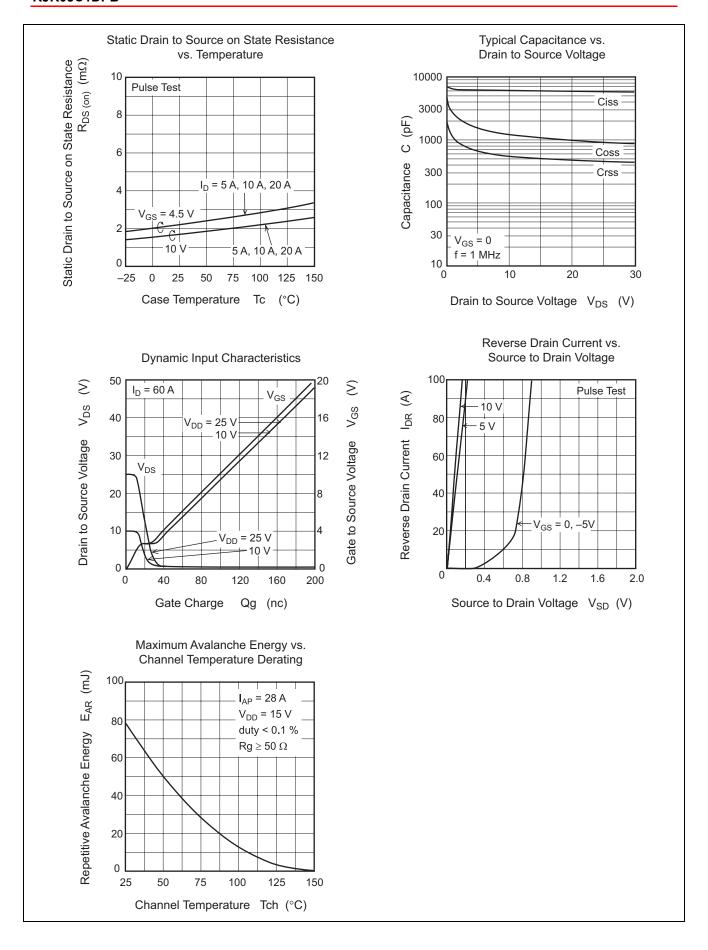
 $(Ta = 25^{\circ}C)$

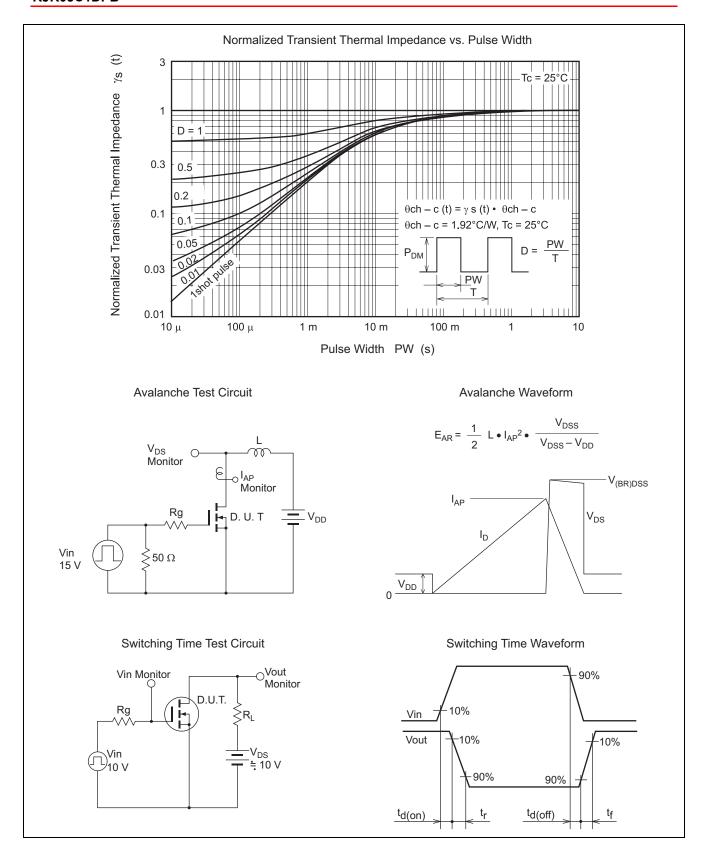
Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain to source breakdown	V _{(BR)DSS}	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
voltage							
Gate to source leak current	I_{GSS}		_	±0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I_{DSS}		_	1	m A	$V_{DS} = 30 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Static drain to source on state	R _{DS(on)}		1.7	2.2	mΩ	$I_D = 30 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$	
resistance	R _{DS(on)}		2.2	3.1	mΩ	$I_D = 30 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$	
Forward transfer admittance	y _{fs}	_	120	_	S	$I_D = 30 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$	
Input capacitance	Ciss	_	6000	_	pF	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	
Output capacitance	Coss	_	1230	_	pF		
Reverse transfer capacitance	Crss	_	550	_	pF		
Gate Resistance	Rg	_	0.5	_	Ω		
Total gate charge	Qg	_	42	_	nC	$V_{DD} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$	
Gate to source charge	Qgs	_	18	_	nC	I _D = 60 A	
Gate to drain charge	Qgd	_	16	_	nC		
Turn-on delay time	t _{d(on)}	_	18	_	ns	V _{GS} = 10 V, I _D = 30 A,	
Rise time	t _r	_	19	_	ns	$V_{DD} \cong 10 \text{ V}, R_L = 0.33 \Omega,$ $Rg = 4.7 \Omega$	
Turn-off delay time	$t_{\sf d(off)}$		75	_	ns		
Fall time	t _f	_	15	_	ns		
Body-drain diode forward voltage	V_{DF}	_	0.39	_	V	I _F = 2 A, V _{GS} = 0 Note4	
Body-drain diode reverse	t _{rr}	_	40	_	ns	I _F = 60 A, V _{GS} = 0	
recovery time						$di_F/dt = 100 A/ \mu s$	

Notes: 4. Pulse test

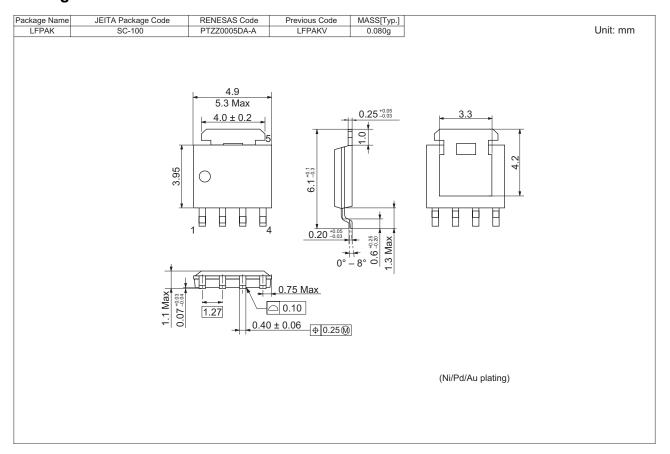
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK03C1DPB-00-J5	2500 pcs	Taping

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